

Amendments to the Specification:

Please replace the paragraph beginning at page 6, line 16 with the following amended paragraph:

-- According to the exemplary embodiment, a thin-layer LED chip 4 [[5 ]] is prepared, comprising an epitaxial layer sequence 6 that is disposed on a carrier element 2 and contains an electromagnetic-radiation-generating active region 8, and a reflective layer 3 that is disposed on a principal surface of the epitaxial layer sequence 6 facing toward the carrier element 2 and reflects at least a portion of the electromagnetic radiation generated in the epitaxial layer sequence 6 back thereinto (see FIG. 1a). It should be noted that for the sake of simplicity only one thin-layer LED chip 4 [[5 ]] is referred to here. In large-scale chip production, the thin-layer LED chips are usually prepared and processed further in the as yet unsingulated state, that is, on a wafer comprising a plurality of in principle similar thin-layer LED chips that are not singulated into mutually separate thin-layer LED chips until a subsequent stage. --

Please replace the paragraph beginning at page 7, line 3 with the following amended paragraph:

-- Apart from spin-on glass, additional glass materials or other materials transparent to a radiation generated in the epitaxial layer sequence 6 can also be structured by grayscale lithography 10. Spin-on glass is particularly well suited for this process, however. --